

# MBR1635, MBR1645, MBRB1645, NRVBB1645

## Switch Mode Power Rectifiers

### 16 A, 35 and 45 V

These state-of-the-art devices use the Schottky Barrier principle with a platinum barrier metal.

#### Features

- Guard-ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams for TO-220  
1.7 Grams for D<sup>2</sup>PAK
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:  
260°C Max. for 10 Seconds

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$		V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$	35	
	MBR1635	45	
	MBRB1645	45	
Average Rectified Forward Current Delay (Rated $V_R$ , $T_C = 163^\circ\text{C}$ ) Total Device	$I_{F(AV)}$	16	A
Peak Repetitive Forward Current, Per Leg (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 157^\circ\text{C}$ ) Total Device	$I_{FRM}$	32	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	1.0	A
Storage Temperature Range	$T_{stg}$	-65 to +175	°C
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	°C
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

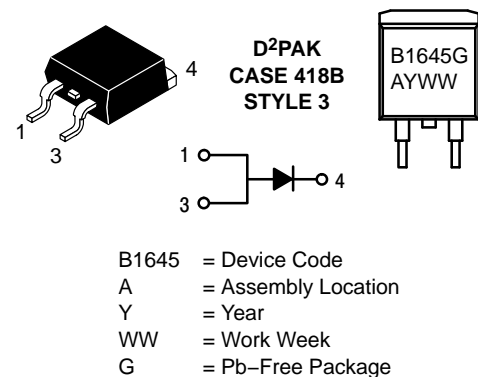
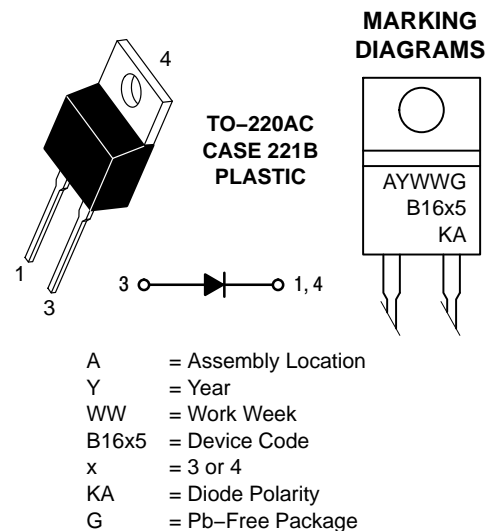
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_J/dT_J < 1/R_{\theta JA}$ .



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#### ORDERING INFORMATION

Device	Package	Shipping
MBR1635G	TO-220 (Pb-Free)	50 Units / Rail
MBR1645G	TO-220 (Pb-Free)	50 Units / Rail
MBRB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail
NRVBB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail

# MBR1635, MBR1645, MBRB1645, NRVBB1645

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.5	$^{\circ}\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 16$ Amps, $T_C = 125^{\circ}\text{C}$ ) ( $i_F = 16$ Amps, $T_C = 25^{\circ}\text{C}$ )	$V_F$	0.57 0.63	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}\text{C}$ ) (Rated dc Voltage, $T_C = 25^{\circ}\text{C}$ )	$i_R$	40 0.2	mA

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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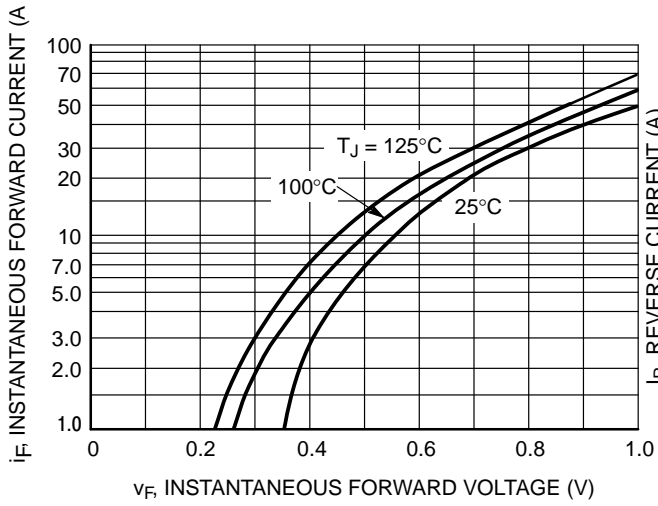


Figure 1. Typical Forward Voltage

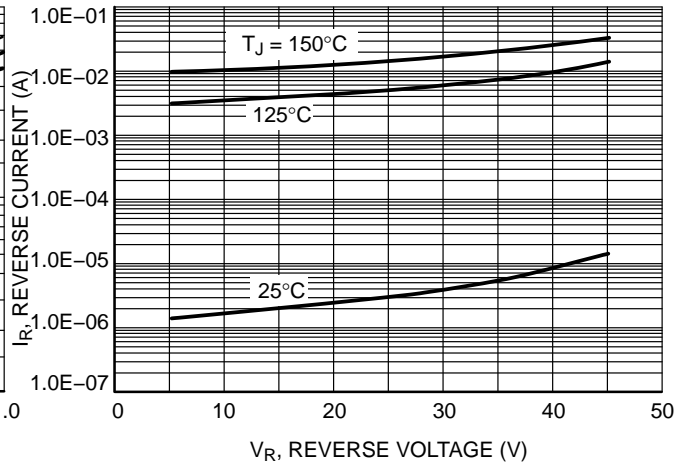


Figure 2. Typical Reverse Current

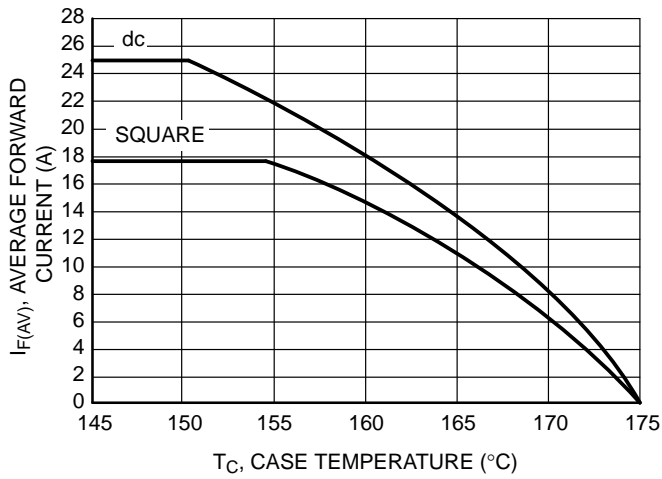


Figure 3. Current Derating, Case, Per Leg

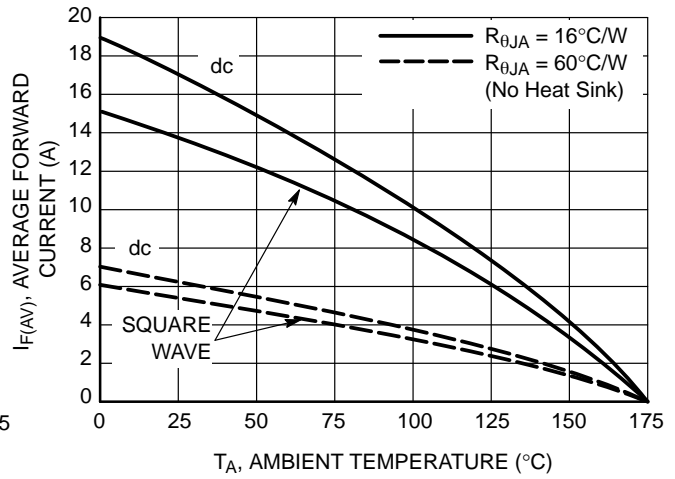


Figure 4. Current Derating, Ambient

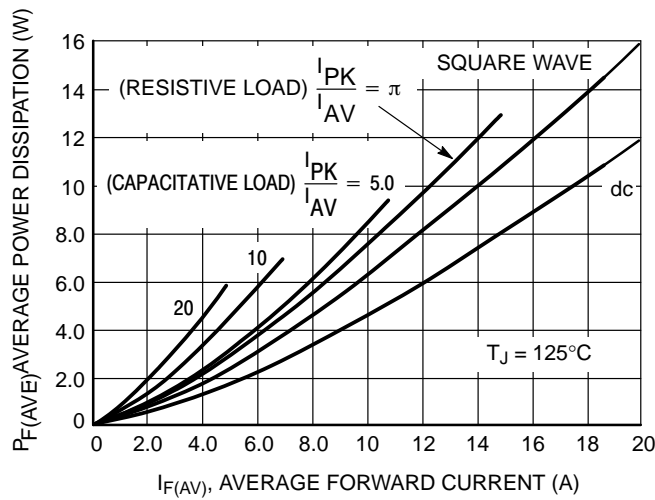


Figure 5. Forward Power Dissipation

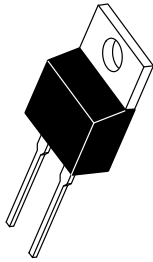
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

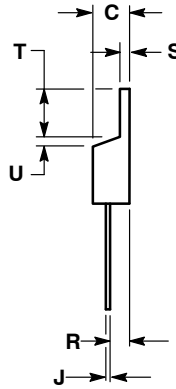
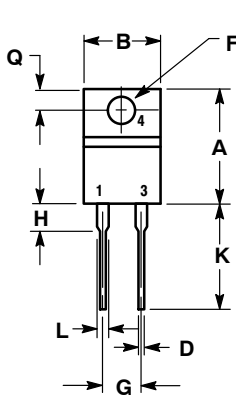


### TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013



SCALE 1:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STYLE 1:  
PIN 1. CATHODE  
2. N/A  
3. ANODE  
4. CATHODE

STYLE 2:  
PIN 1. ANODE  
2. N/A  
3. CATHODE  
4. ANODE

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

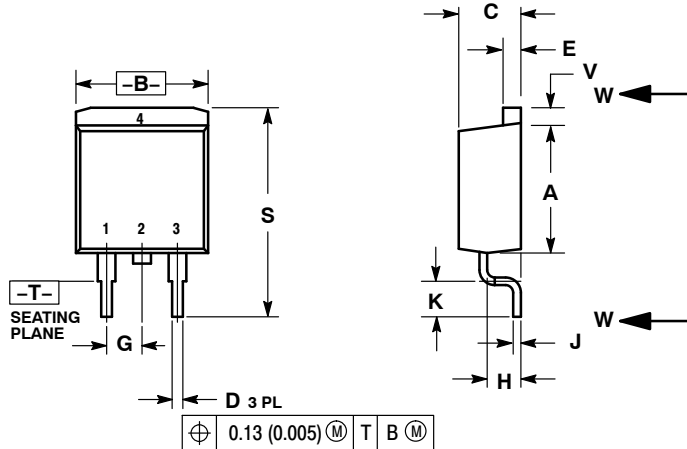
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

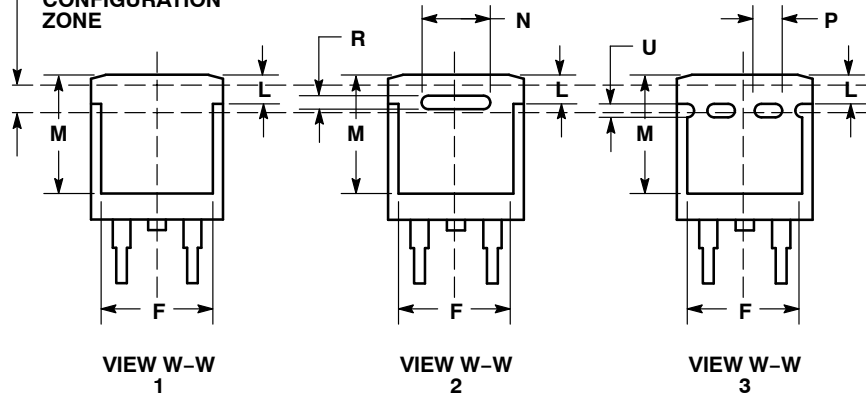


**NOTES:**

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE CONFIGURATION ZONE**



<b>STYLE 1:</b> PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	<b>STYLE 2:</b> PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	<b>STYLE 3:</b> PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	<b>STYLE 4:</b> PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	<b>STYLE 5:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE	<b>STYLE 6:</b> PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE
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**MARKING INFORMATION AND FOOTPRINT ON PAGE 2**

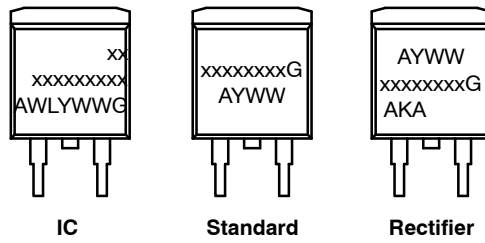
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

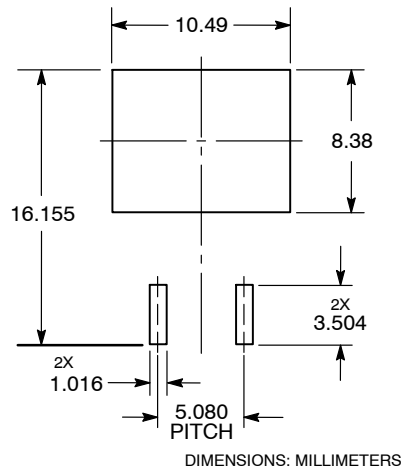
**GENERIC  
MARKING DIAGRAM\***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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